

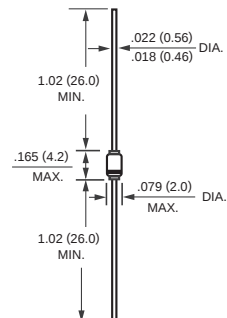
SCHOTTKY DIODES

FEATURES

- * Fast Switching Device($T_{RR}<4.0nS$)
- * DO-35 Package (JEDEC)
- * Through-Hole Device Type Mounting
- * Hermetically Sealed Glass
- * Compression Bonded Construction
- * All external surfaces are corrosion resistant and leads are readily solderable

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25 °C ambient temperature unless otherwise specified.
Single phase, half wave, 60 Hz, resistive or inductive load.
For capacitive load, derate current by 20%.



Dimensions in inches and (millimeters)

MAXIMUM RATINGS (@ $T_A = 25^\circ\text{C}$ unless otherwise noted)

RATINGS	SYMBOL	BAT85	UNITS
Maximum Forward Continuous Reverse Voltage	V_R	30	V
Maximum Forward Continuous Current @ $T_A=25^\circ\text{C}$	I_F	200	mAmps
Maximum Peak Forward Current @ $T_A=25^\circ\text{C}$	I_{FM}	300	mAmps
Surge Forward Current @ $t_p<1s, T_A=25^\circ\text{C}$	I_{FSM}	600	mAmps
Maximum Power Dissipation @ $T_A=65^\circ\text{C}$	P_D	200	mW
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to + 125	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (@ $T_A = 25^\circ\text{C}$ unless otherwise noted)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNITS
Reverse breakdown voltage ($I_R=10\mu\text{A}$)	$V_{(BR)R}$	30	-	-	V
Reverse voltage leakage current ($V_R=25\text{V}$)	I_R	-	-	2	μA
Forward voltage Pulse Test $t_p<300\mu\text{s}, \delta<2\%$ ($I_F=0.1\text{mA}$) ($I_F=1\text{mA}$) ($I_F=10\text{mA}$) ($I_F=30\text{mA}$) ($I_F=100\text{mA}$)	V_F	-	- - - 0.5 -	0.24 0.32 0.4 - 0.8	V
Diode capacitance ($V_R=1\text{V}, f=1\text{MHz}$)	C_T	-	-	10	pF
Reverse recovery time ($I_F=I_R=10\text{mA}, I_R=1\text{mA}$)	t_{rr}	-	-	5	nS